

20 V, N-channel Trench MOSFET 9 March 2016

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	-	6.3	А
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 6.3 A; T _j = 25 °C		-	16	20	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G G S S 017aaa255

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMV20XNEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV20XNEA	DT%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

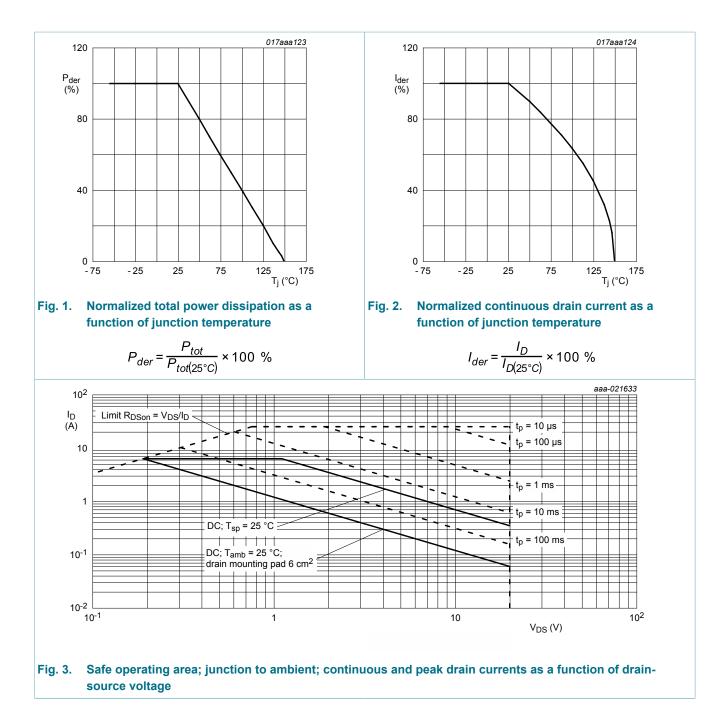
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-12	12	V
ID	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	6.3	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	25	А
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 1.6 A; DUT in avalanche (unclamped)		-	16	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	0.46	W
			[1]	-	1.19	W
		T _{sp} = 25 °C		-	6.94	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	0.73	А
ESD maxim	num rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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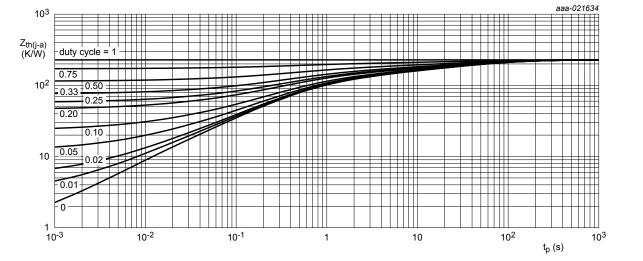
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9. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	227	270	K/W
	from junction to ambient		[2]	-	91	105	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	13	18	K/W

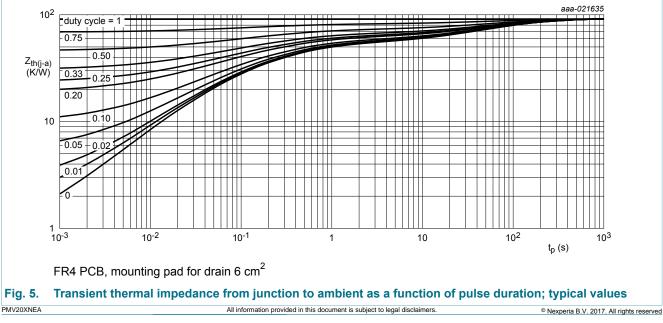
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint





Product data sheet

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	L				
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	0.75	1	1.25	V
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 6.3 A; T _j = 25 °C	-	16	20	mΩ
resistance	resistance	V _{GS} = 4.5 V; I _D = 6.3 A; T _j = 150 °C	-	24	30	mΩ
		V_{GS} = 2.5 V; I _D = 4.8 A; T _j = 25 °C	-	24	34	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 6.3 A; T _j = 25 °C	-	26.8	-	S
R _G	gate resistance	f = 1 MHz	-	7.2	-	Ω
Dynamic ch	aracteristics	· · ·				
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I _D = 6.3 A; V _{GS} = 4.5 V;	-	9.9	15	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.4	-	nC
Q _{GD}	gate-drain charge		-	3.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	930	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	178	-	pF
C _{rss}	reverse transfer capacitance		-	144	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I _D = 6.3 A; V _{GS} = 4.5 V;	-	16	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	40	-	ns
t _{d(off)}	turn-off delay time		-	44	-	ns
t _f	fall time	1	-	22	-	ns
Source-drai	n diode	· · ·	1		-1	
V _{SD}	source-drain voltage	I _S = 0.9 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

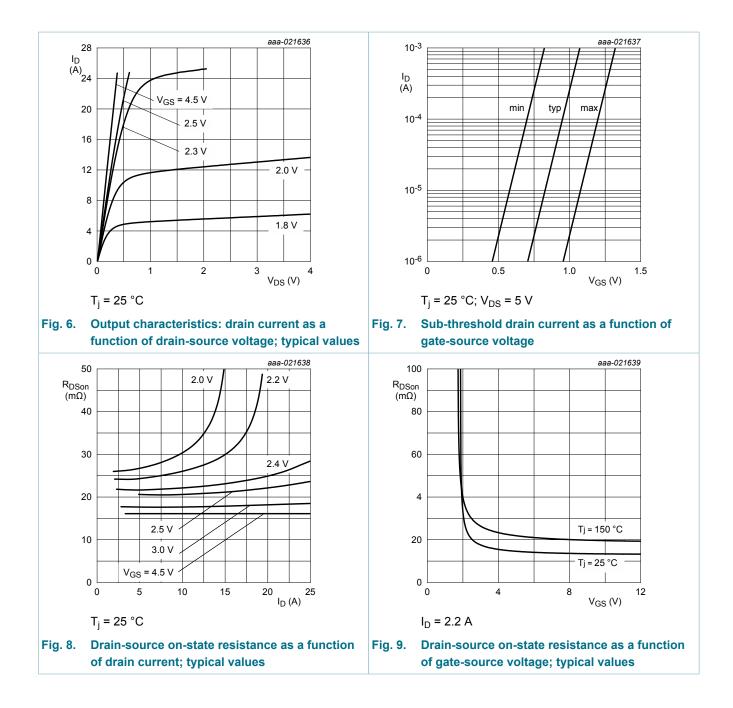
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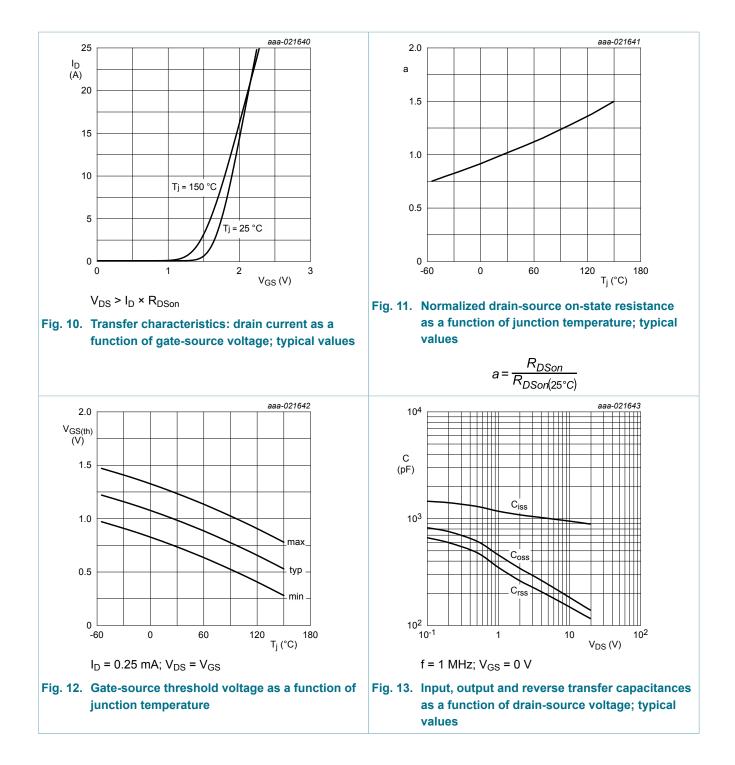
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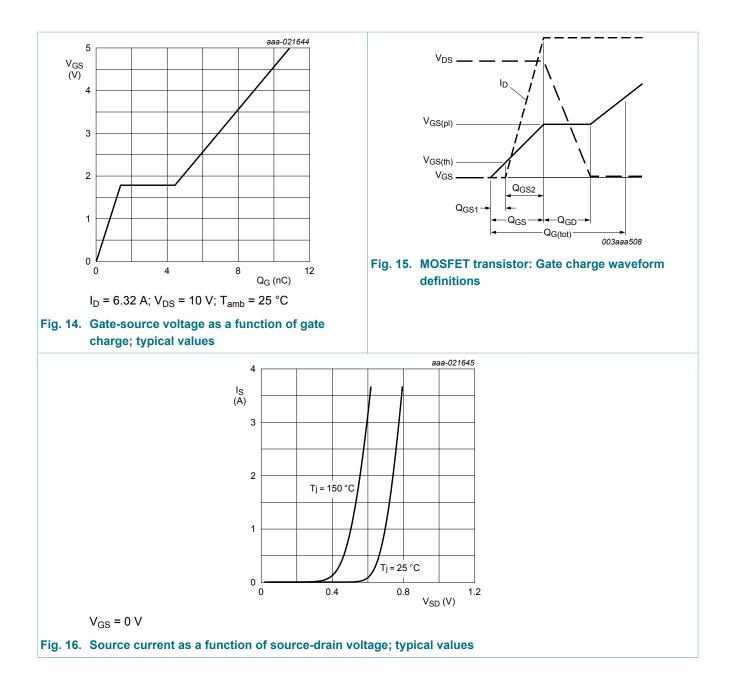
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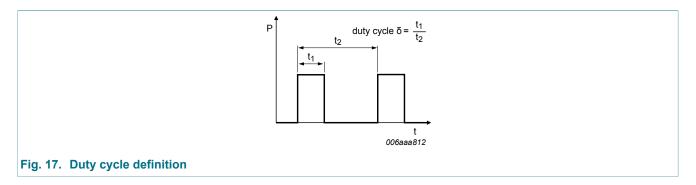
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11. Test information

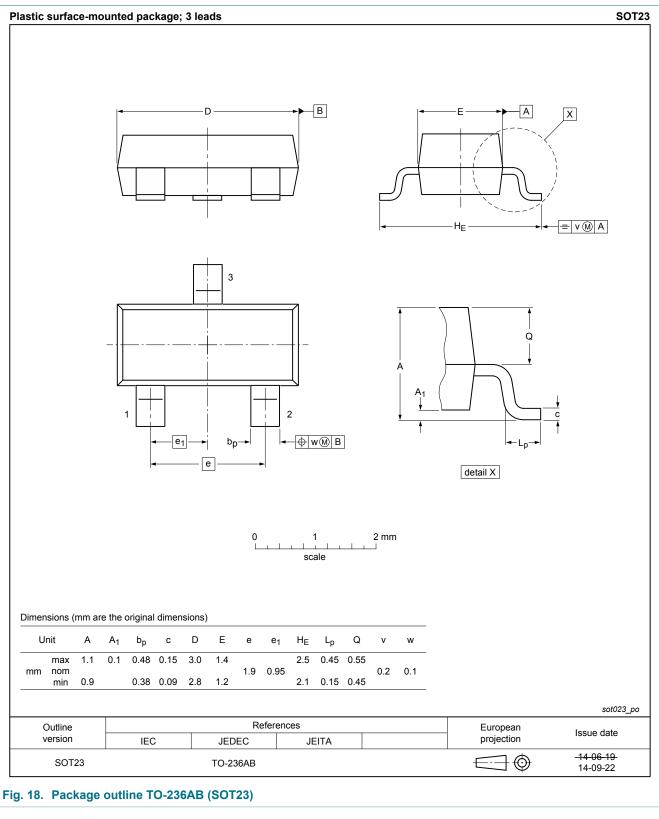


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



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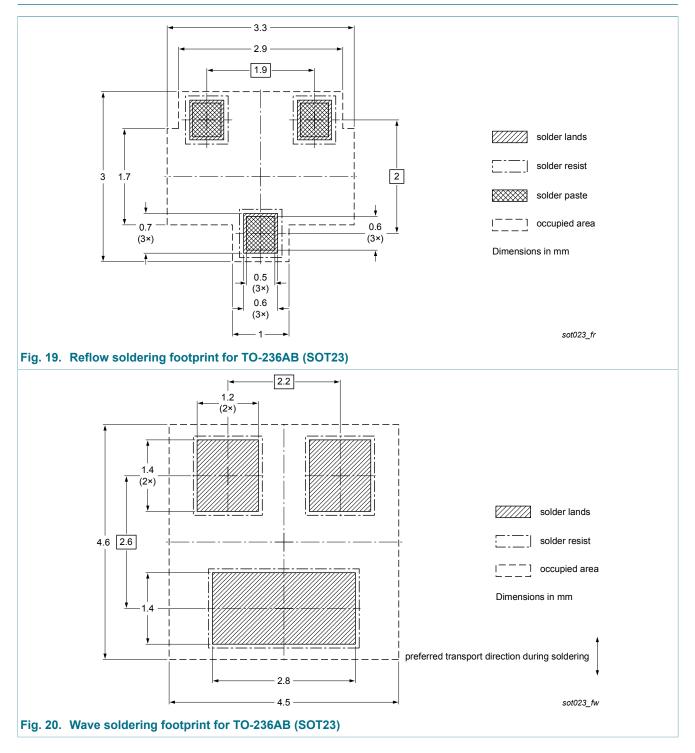
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13. Soldering



PMV20XNEA

14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV20XNEA v.1	20160309	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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